Abstracts

A New Via Hole Structure for Power GaAs MESFET's and MMIC

L. Songfa and L. Qingxiang. "A New Via Hole Structure for Power GaAs MESFET's and MMIC." 1983 Microwave and Millimeter-Wave Monolithic Circuits Symposium Digest 83.1 (1983 [MCS]): 36-36.

A New Via Hole Structure made by the laser beam technique has been developed. A 1.2mm gate width GaAs power MESFETand an experimental MMIC were fabricated with this method, thus the availability of this new via hole structure has been verified.

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